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17. The method according to claim 14, further comprising:
heat-treating the semiconductor layer while maintaining the
temperature of the substrate in a range of 50 to 150°C after the
semiconductor layer is formed by depositing the organic semiconductor.

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18. The method according to claim 14, further comprising:
forming an electrode by depositing an electrode material on the
semiconductor layer while maintaining the temperature of the substrate at
45°C or less after the semiconductor layer is formed by depositing the organic semiconductor.

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19. An active matrix display comprising: a plurality of the organic thin film transistors according to claim 1 as switching elements for pixels.

 A radio recognition tag comprising: an integrated circuit portion,

wherein the integrated circuit portion comprises the organic thin film transistor according to claim 1.

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